Reza Ghandi

List of Publications by Year
in descending order

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23	424	1040056 9	1058476 14
papers	citations	h-index	g-index

23	23	23	225
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	4.5kV SiC Charge-Balanced MOSFETs with Ultra-Low On-Resistance. , 2020, , .		17
2	3kV SiC Charge-Balanced Diodes Breaking Unipolar Limit. , 2019, , .		8
3	Design and Characterization of High-Temperature ECL-Based Bipolar Integrated Circuits in 4H-SiC. IEEE Transactions on Electron Devices, 2012, 59, 1076-1083.	3.0	56
4	Surface-Passivation Effects on the Performance of 4H-SiC BJTs. IEEE Transactions on Electron Devices, 2011, 58, 259-265.	3.0	57
5	Modeling and Characterization of the on-Resistance in 4H-SiC Power BJTs. IEEE Transactions on Electron Devices, 2011, 58, 2081-2087.	3.0	20
6	High-Voltage (2.8 kV) Implantation-Free 4H-SiC BJTs With Long-Term Stability of the Current Gain. IEEE Transactions on Electron Devices, 2011, 58, 2665-2669.	3.0	26
7	High Voltage, Low On-Resistance 4H-SiC BJTs with Improved Junction Termination Extension. Materials Science Forum, 2011, 679-680, 706-709.	0.3	8
8	(Invited) Silicon Carbide Bipolar Power Devices. ECS Transactions, 2011, 41, 189-200.	0.5	0
9	Measurements and Simulations of Lateral PNP Transistors in a SiC NPN BJT Technology for High Temperature Integrated Circuits. Materials Science Forum, 2011, 679-680, 758-761.	0.3	1
10	Modeling and Characterization of Current Gain Versus Temperature in 4H-SiC Power BJTs. IEEE Transactions on Electron Devices, 2010, 57, 704-711.	3.0	56
11	Influence of Emitter Width and Emitterâ€"Base Distance on the Current Gain in 4H-SiC Power BJTs. IEEE Transactions on Electron Devices, 2010, 57, 2664-2670.	3.0	26
12	Experimental Evaluation of Different Passivation Layers on the Performance of 3kV 4H-SiC BJTs. Materials Science Forum, 2010, 645-648, 661-664.	0.3	7
13	SiC Bipolar Power Transistors - Design and Technology Issues for Ultimate Performance. Materials Research Society Symposia Proceedings, 2010, 1246, 1.	0.1	5
14	Effect of 3.0â€‰MeV helium implantation on electrical characteristics of 4H-SiC BJTs. Physica Scripta, 2010, T141, 014012.	2.5	4
15	High-Voltage 4H-SiC PiN Diodes With Etched Junction Termination Extension. IEEE Electron Device Letters, 2009, 30, 1170-1172.	3.9	55
16	High-Current-Gain SiC BJTs With Regrown Extrinsic Base and Etched JTE. IEEE Transactions on Electron Devices, 2008, 55, 1894-1898.	3.0	18
17	Fabrication of 2700-V 12-$hbox{m}Omega cdot hbox{cm}^{2}$ Non Ion-Implanted 4H-SiCBJTs With Common-Emitter Current Gain of 50. IEEE Electron Device Letters, 2008, 29, 1135-1137.	3.9	35
18	Bipolar Integrated OR-NOR Gate in 4H-SiC. Materials Science Forum, 0, 717-720, 1257-1260.	0.3	2

#	Article	IF	Citations
19	Fabrication of 2.5kV 4H-SiC PiN Diodes with High Energy Implantation (>12MeV) of Al⁺ and B⁺. Materials Science Forum, 0, 924, 573-576.	0.3	4
20	Deep Level Transient Spectroscopy (DLTS) Study of 4H-SiC Schottky Diodes and PiN Diodes. Materials Science Forum, 0, 963, 516-519.	0.3	4
21	SiC Charge-Balanced Devices Offering Breakthrough Performance Surpassing the 1-D Ron versus BV Limit. Materials Science Forum, 0, 963, 655-659.	0.3	12
22	A Subcircuit SPICE Model for SiC Charge-Balance Schottky Diodes. Materials Science Forum, 0, 1004, 945-952.	0.3	1
23	Dynamic Switching of 3kV 4H-SiC Charge-Balanced Junction Barrier Schottky (JBS) Diodes. Materials Science Forum, 0, 1004, 939-944.	0.3	2